



11-09-04

IFW

Atty. Dkt. No. 039153-0690

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: James N. PAN, et al.

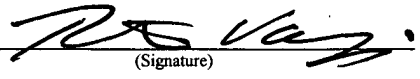
Title: STRAINED SILICON MOSFETS  
HAVING IMPROVED THERMAL  
DISSIPATION

Appl. No.: 10/658,963

Filing Date: 09/09/2003

Examiner: N. W. HA

Art Unit: 2814

CERTIFICATE OF EXPRESS MAILING	
I hereby certify that this correspondence is being deposited with the United States Postal Service's "Express Mail Post Office To Addressee" service under 37 C.F.R. § 1.10 on the date indicated below and is addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.	
EV 445625775 US (Express Mail Label Number)	November 8, 2004 (Date of Deposit)
Ruthie Vallejo (Printed Name)	
 (Signature)	

**RESPONSE TO RESTRICTION REQUIREMENT**Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In response to the restriction requirement set forth in the Office Action mailed November 1, 2004, Applicant hereby provisionally elects Group II, Claims 6-20, drawn to a method of making a semiconductor device, classified in class 438, subclass 752. Applicant reserves the right to file a divisional application on the non-elected claims.

Respectfully submitted,

Date 8 November 2004By Ronald CoslickFOLEY & LARDNER LLP  
Customer Number: 23392  
Telephone: (310) 975-7964  
Facsimile: (310) 557-8475Ronald Coslick  
Attorney for Applicant  
Registration No. 36,489